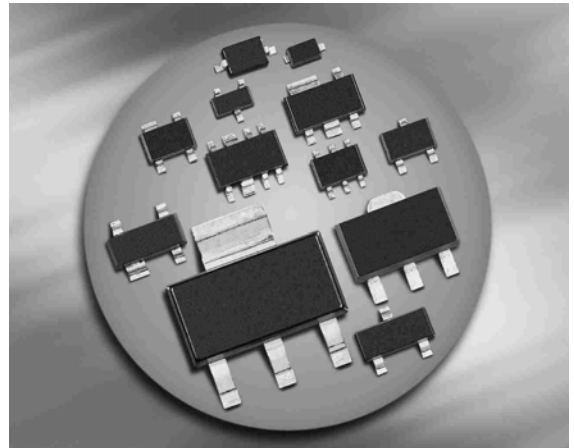
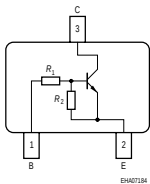


NPN Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ($R_1=4.7k\Omega$, $R_2=10k\Omega$)


BCR114/F
BCR114L3/T


Type	Marking	Pin Configuration						Package
BCR114	U4s	1=B	2=E	3=C	-	-	-	SOT23
BCR114F	U4s	1=B	2=E	3=C	-	-	-	TSFP-3
BCR114L3	U4	1=B	2=E	3=C	-	-	-	TSLP-3-4
BCR114T	U4s	1=B	2=E	3=C	-	-	-	SC75

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Emitter-base voltage	V_{EBO}	5	
Input on voltage	$V_{I(on)}$	15	
Collector current	I_C	100	mA
Total power dissipation- BCR114, $T_S \leq 102^\circ\text{C}$ BCR114F, $T_S \leq 128^\circ\text{C}$ BCR114L3, $T_S \leq 135^\circ\text{C}$ BCR114T, $T_S \leq 109^\circ\text{C}$	P_{tot}	200 250 250 250	mW
Junction temperature	T_j	150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BCR114		≤ 240	
BCR114F		≤ 90	
BCR114L3		≤ 60	
BCR114T		≤ 165	

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

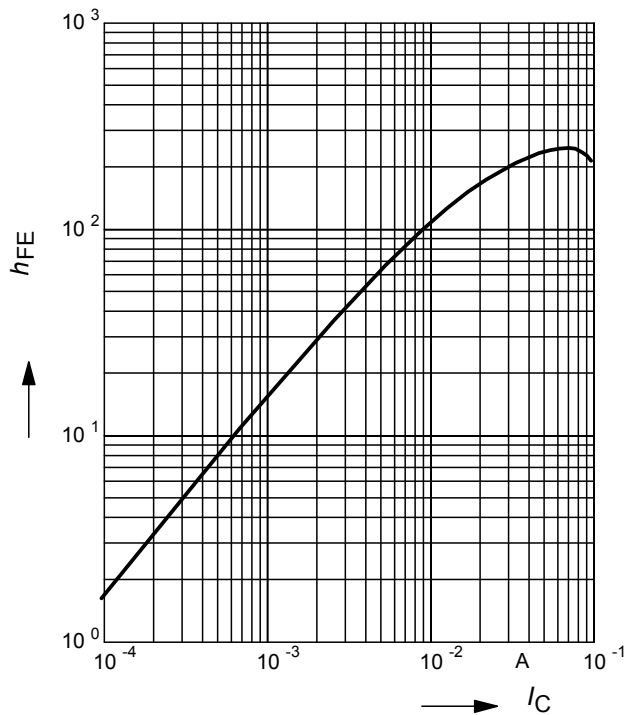
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 100\ \mu\text{A}$, $I_B = 0$	$V_{(\text{BR})\text{CEO}}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10\ \mu\text{A}$, $I_E = 0$	$V_{(\text{BR})\text{CBO}}$	50	-	-	
Collector-base cutoff current $V_{\text{CB}} = 40\ \text{V}$, $I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{\text{EB}} = 5\ \text{V}$, $I_C = 0$	I_{EBO}	-	-	520	μA
DC current gain ¹⁾ $I_C = 5\ \text{mA}$, $V_{\text{CE}} = 5\ \text{V}$	h_{FE}	30	-	-	-
Collector-emitter saturation voltage ¹⁾ $I_C = 10\ \text{mA}$, $I_B = 0.5\ \text{mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100\ \mu\text{A}$, $V_{\text{CE}} = 5\ \text{V}$	$V_{\text{i(off)}}$	0.5	-	1.1	
Input on voltage $I_C = 2\ \text{mA}$, $V_{\text{CE}} = 0.3\ \text{V}$	$V_{\text{i(on)}}$	0.5	-	1.4	
Input resistor	R_1	3.2	4.7	6.2	k Ω
Resistor ratio	R_1/R_2	0.42	0.47	0.52	-
AC Characteristics					
Transition frequency $I_C = 10\ \text{mA}$, $V_{\text{CE}} = 5\ \text{V}$, $f = 100\ \text{MHz}$	f_{T}	-	160	-	MHz
Collector-base capacitance $V_{\text{CB}} = 10\ \text{V}$, $f = 1\ \text{MHz}$	C_{cb}	-	3	-	pF

¹⁾Pulse test: $t < 300\ \mu\text{s}$; $D < 2\%$

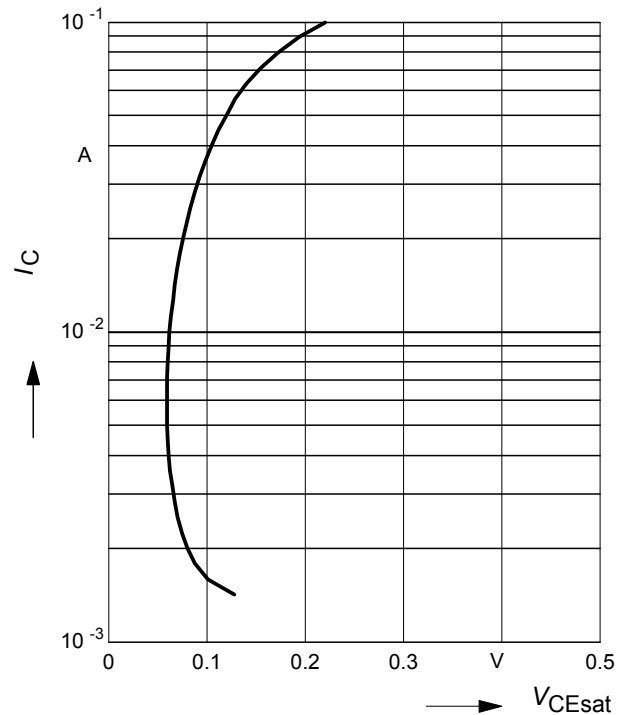
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5\text{ V}$ (common emitter configuration)



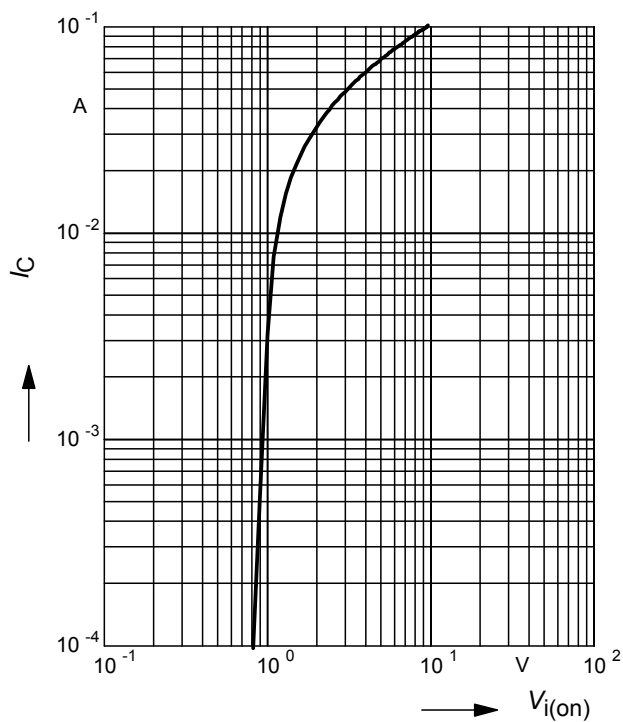
Collector-emitter saturation voltage

$V_{CEsat} = f(I_C), h_{FE} = 20$



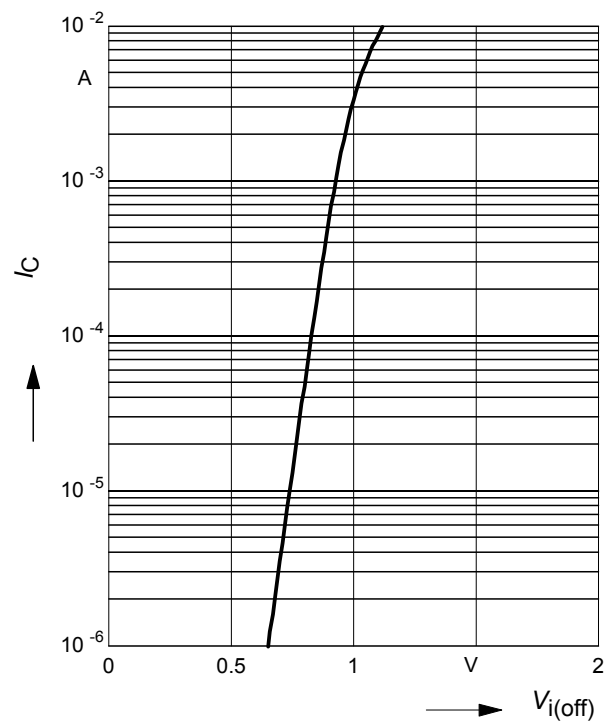
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3\text{ V}$ (common emitter configuration)



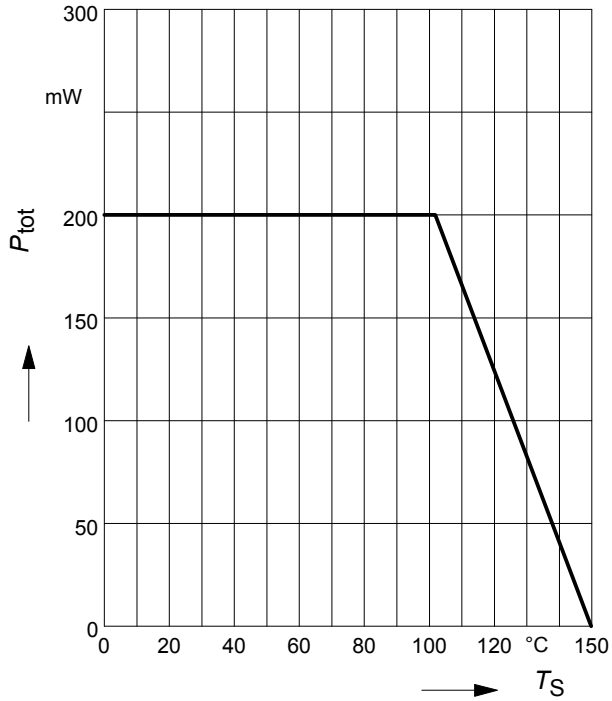
Input off voltage $V_{i(off)} = f(I_C)$

$V_{CE} = 5\text{ V}$ (common emitter configuration)



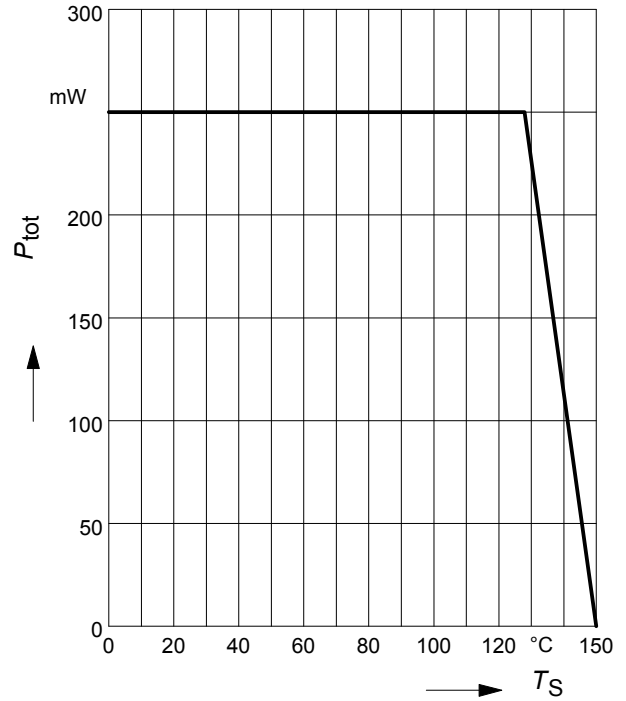
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR114



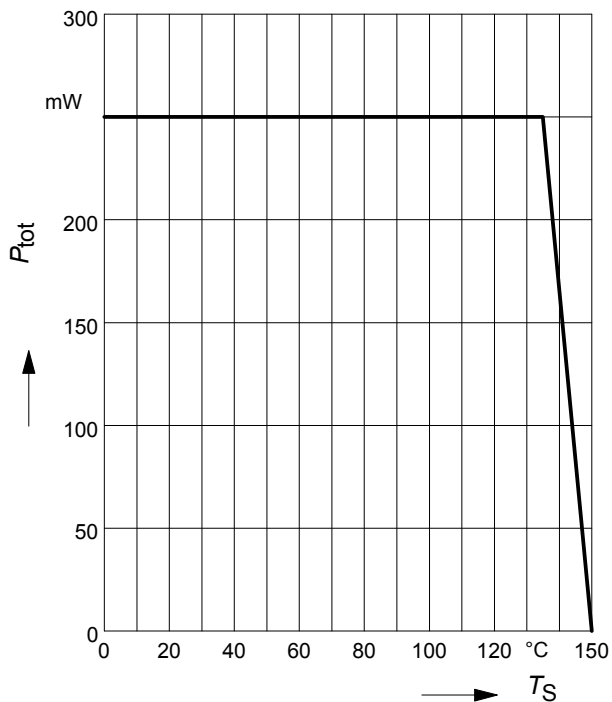
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR114F



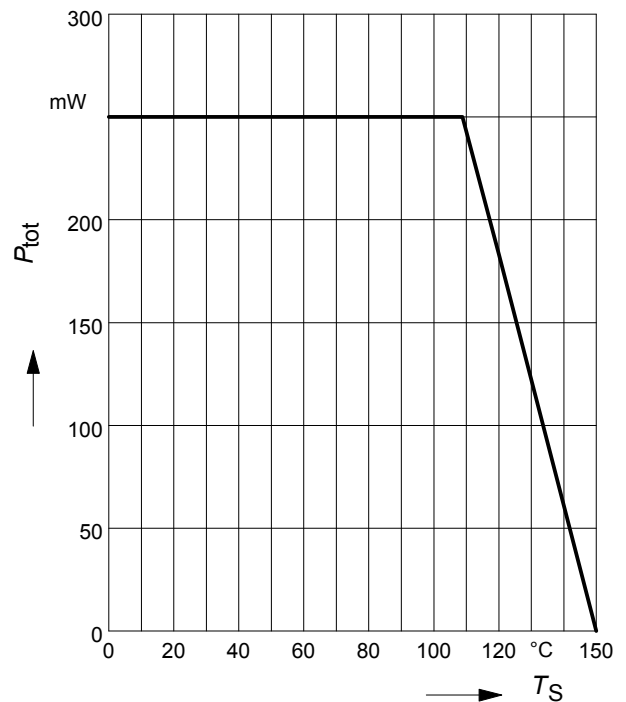
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR114L3



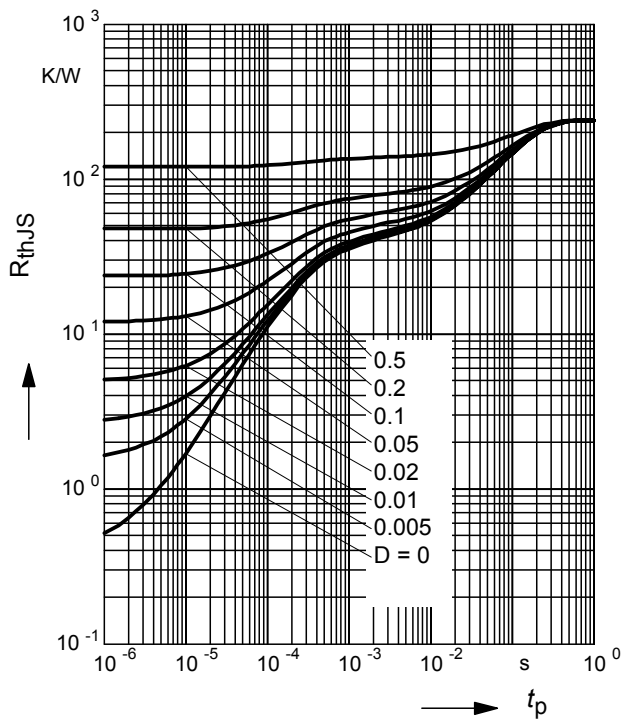
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR114T



Permissible Pulse Load $R_{thJS} = f(t_p)$

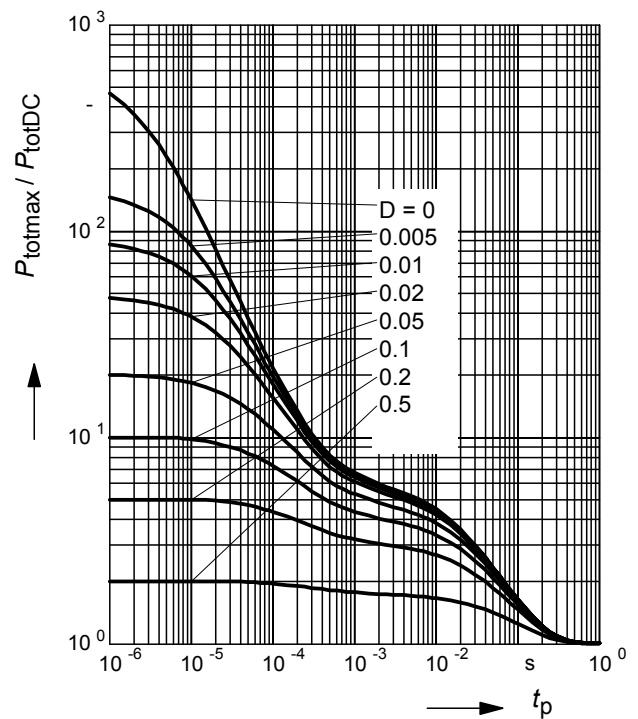
BCR114



Permissible Pulse Load

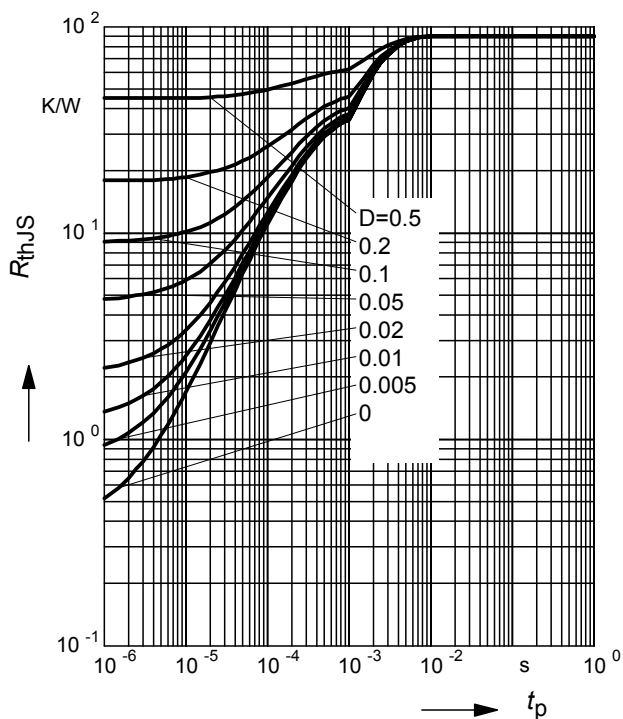
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR114



Permissible Puls Load $R_{thJS} = f(t_p)$

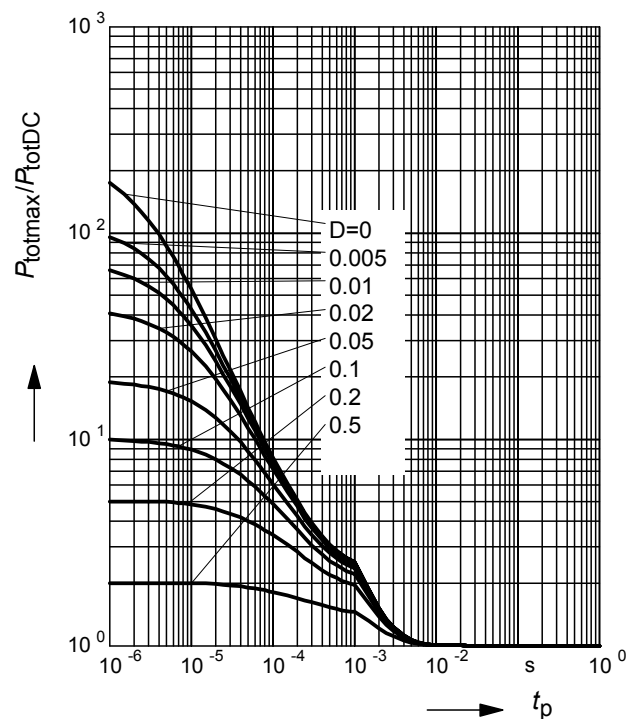
BCR114F



Permissible Pulse Load

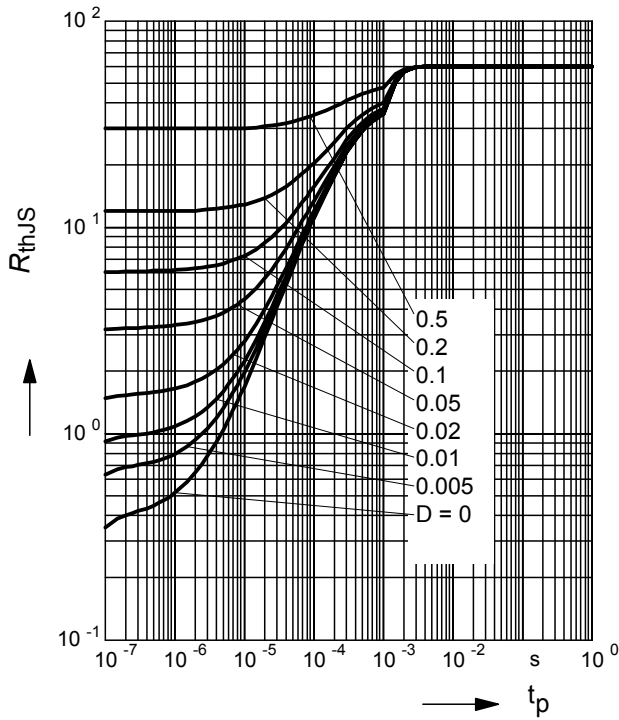
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR114F



Permissible Puls Load $R_{thJS} = f(t_p)$

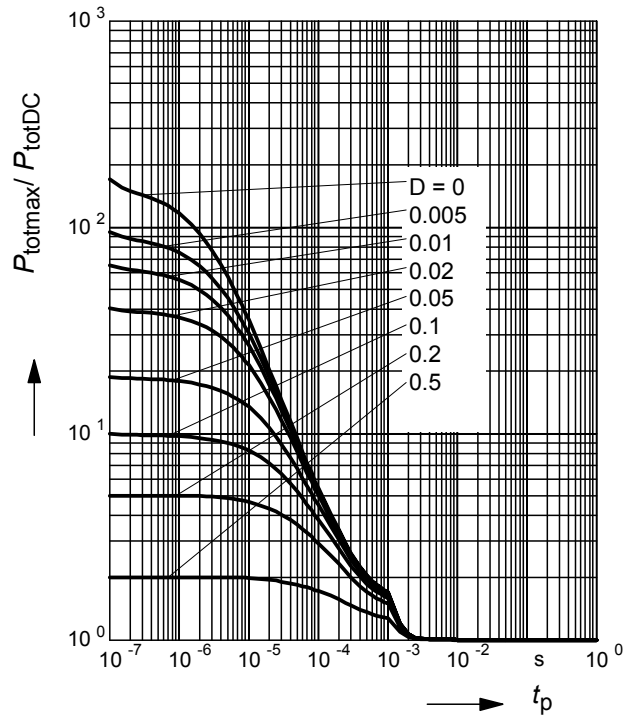
BCR114L3



Permissible Pulse Load

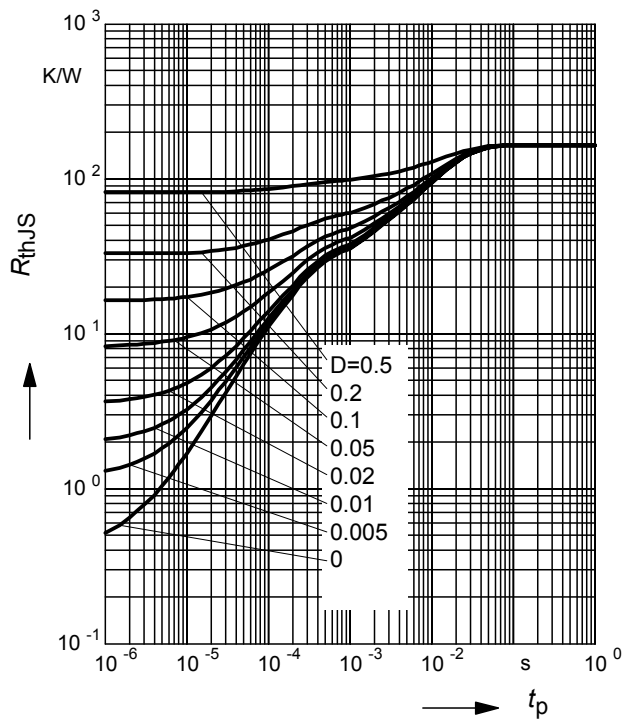
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR114L3



Permissible Puls Load $R_{thJS} = f(t_p)$

BCR114T



Permissible Pulse Load

$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR114T

